Abstracts

High Power Microstrip RF Switches

S.D. Choi and J.F. Boreham. "High Power Microstrip RF Switches." 1972 G-MTT International Microwave Symposium Digest of Technical Papers 72.1 (1972 [MWSYM]): 52-54.

A microstrip-type SPDT switch, using only two PIN diodes and eliminating usual dc blocking capacitors, has demonstrated an RF power handling capacity greater than 100 W CW at S-band. The insertion loss is less than 0.25 dB and the input-to-off port isolation is greater than 36 dB over a bandwidth larger than 30 MHz.

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